ABSTRACT

A method of transferring a layer from a first wafer to a second wafer, the first wafer comprising a zone of weakness defining, with a surface of the first wafer, a layer of material selected from semiconductor materials having a thickness that is close to or greater than the thickness of the layer to be transferred, characterized in that it comprises the following steps:

a) bringing the surfaces of the two wafers into contact so that the layer having a thickness that is close to or greater than the thickness of the layer to be transferred is in contact with the second wafer;

b) supplying heat energy at a first temperature that is substantially higher than ambient temperature for a first time period;

c) supplying additional heat energy to increase the temperature above the first temperature to detach the layer to be transferred from the first wafer at the zone of weakness.

The invention also provides an application of said method.

FIG. 1